

PNP General Purpose Amplifier

This device is designed for use as a general purpose amplifier and switch requiring collector currents to 500 mA. Sourced from Process 67. See TN4033A for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V _{CEO}	Collector-Emitter Voltage	60	V	
V _{CBO}	Collector-Base Voltage	60	V	
V _{EBO}	Emitter-Base Voltage	5	V	
lc	Collector Current - Continuous 800 m		mA	
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

Symbol	Characteristic	Мах		Units	
		PN4355	*MMBT4355		
PD	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	mW mW/°C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W	

TA = 25°C unless otherwise noted

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

PNP General Purpose Amplifier (continued)

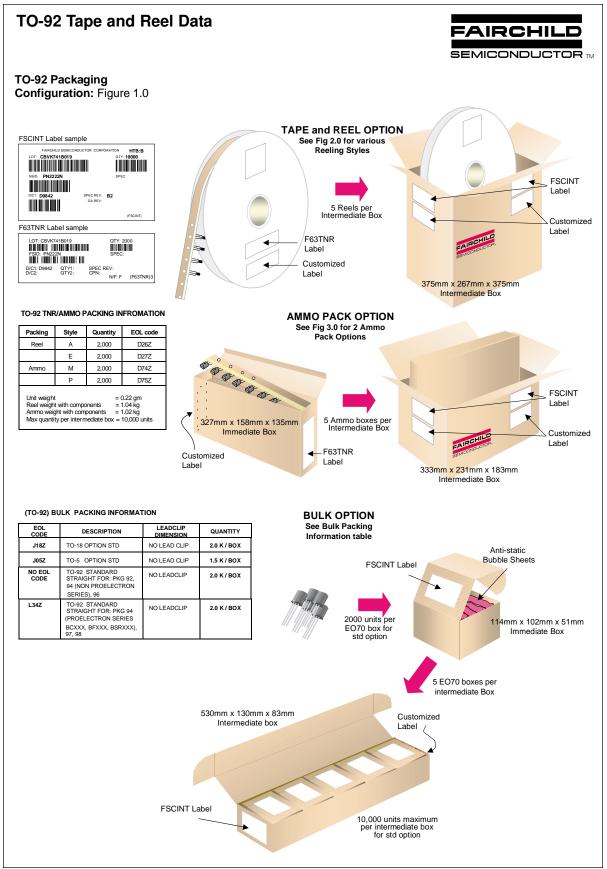
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				<u>.</u>
V _{(BR)CEO}	Collector-Emitter Sustaining Voltage*	$I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0$	60		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 10 \ \mu A, \ I_{\rm E} = 0$	60		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10 \ \mu A, \ I_{\rm C} = 0$	5.0		V
	Collector-Cutoff Current	$V_{CB} = 50 \text{ V}, I_E = 0$		50	nA
I _{CBO}					
I _{CBO} I _{EBO} ON CHAF	ACTERISTICS DC Current Gain	$V_{EB} = 5.0 \text{ V}, V_{CE} = 0$ $V_{EB} = 4.0 \text{ V}, I_{C} = 0$ $I_{C} = 100 \mu\text{A}, V_{CE} = 10 \text{V}$	60	10 100	μA nA
IEBO ON CHAF	Emitter-Cutoff Current	$V_{EB} = 4.0 \text{ V}, I_{C} = 0$	75 100 75	-	•
ON CHAF	Emitter-Cutoff Current ACTERISTICS DC Current Gain	$V_{EB} = 4.0 \text{ V}, I_{C} = 0$ $I_{C} = 100 \ \mu\text{A}, V_{CE} = 10 \text{ V}$ $I_{C} = 1.0 \text{mA}, V_{CE} = 10 \text{ V}$ $I_{C} = 10 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_{C} = 100 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_{C} = 500 \text{ mA}, V_{CE} = 10 \text{ V}$	75 100	400	nA
Debo ON CHAF	Emitter-Cutoff Current	$V_{EB} = 4.0 \text{ V}, I_{C} = 0$ $I_{C} = 100 \ \mu\text{A}, V_{CE} = 10 \text{ V}$ $I_{C} = 1.0 \text{mA}, V_{CE} = 10 \text{ V}$ $I_{C} = 10 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_{C} = 100 \text{ mA}, V_{CE} = 10 \text{ V}$	75 100 75	100	•
ON CHAF hFE V _{CE(sat)}	Emitter-Cutoff Current RACTERISTICS DC Current Gain Collector-Emitter Saturation Voltage	$\begin{split} V_{EB} &= 4.0 \text{ V}, $	75 100 75	400 0.15 0.50 1.0	NA NA V V V
ON CHAF	Emitter-Cutoff Current ACTERISTICS DC Current Gain	$\begin{split} V_{EB} &= 4.0 \text{ V}, $	75 100 75	400 0.15 0.50	NA NA

SMALL	SIGNAL CHARACTERISTICS	i			
Cobo	Output Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		30	pF
Cibo	Input Capacitance	$V_{EB} = 0.5 \text{ V}, I_C = 0, f = 1.0 \text{ MHz}$		110	pF
h _{fe}	Small-Signal Current Gain	I _C = 50 mA, V _{CE} = 10 V, f = 100 MHz	1.0	5.0	
NF	Noise Figure	$\label{eq:LC} \begin{array}{l} I_{C} = 100 \; \mu\text{A}, \; V_{CE} = 10 \; \text{V}, \\ R_{S} = 1.0 \; \text{k}\Omega, \; \text{f} = 1.0 \; \text{kHz}, \\ \text{BW} = 1.0 \; \text{Hz} \end{array}$	1.0	3.0	dB

SWITCHING CHARACTERISTICS

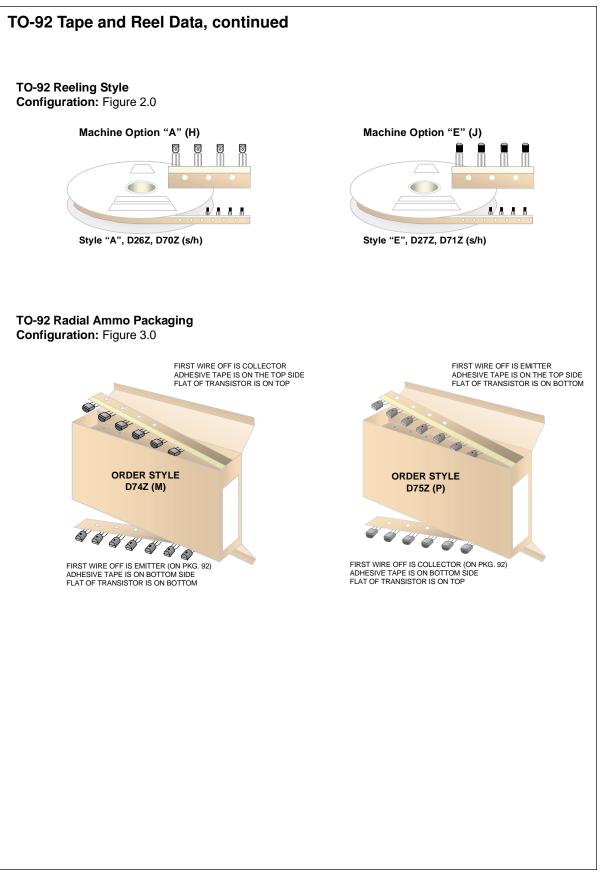
ton	Turn-On Time	$I_{C} = 500 \text{ mA}, V_{CC} = 500 \text{ mA}$	100	ns
toff	Turn-Off Time	$I_{B1} = I_{B2} = 50 \text{ mA}$	400	ns

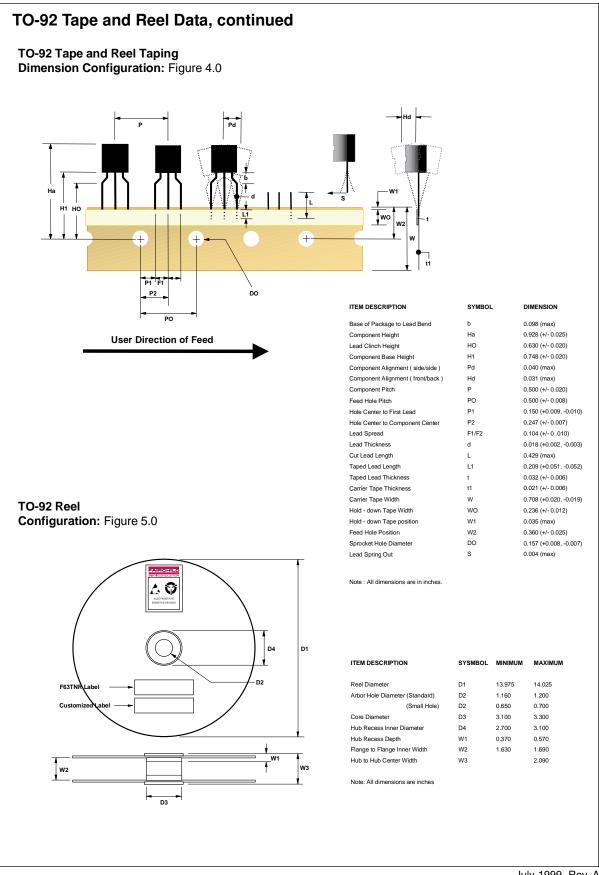
*Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 1.0%



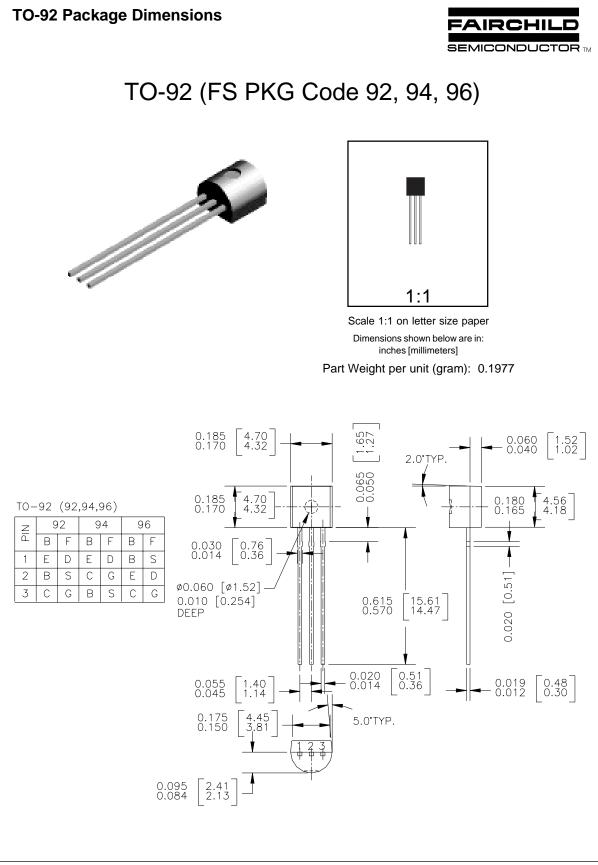
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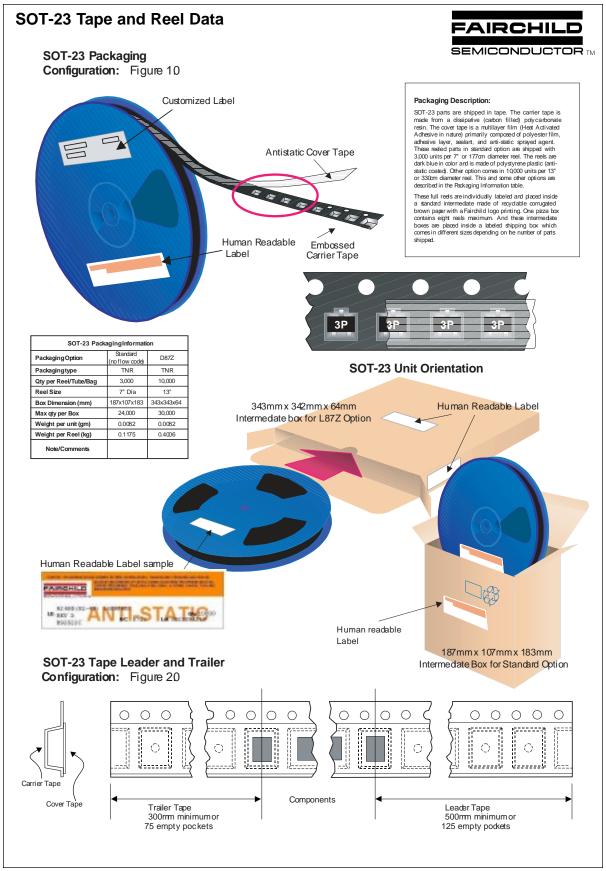
March 2001, Rev. B1





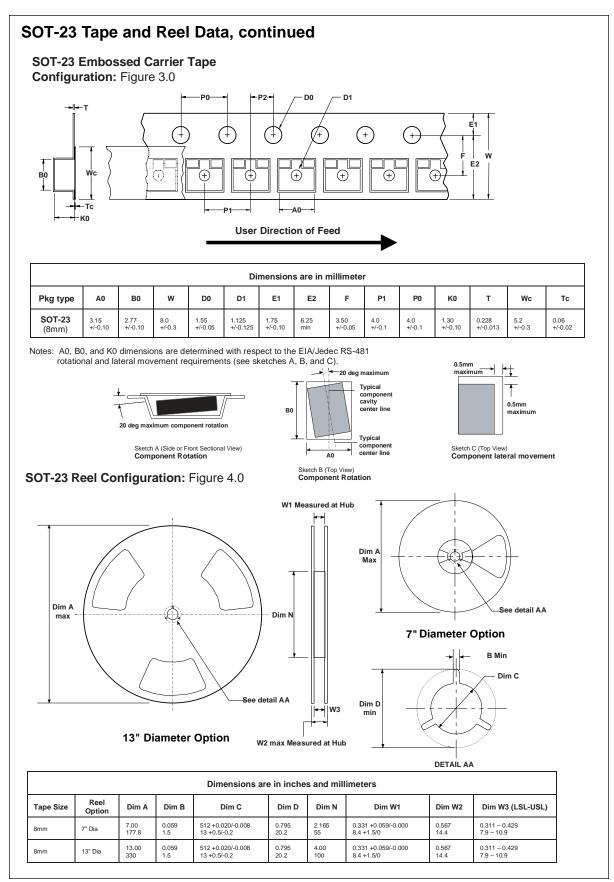
July 1999, Rev. A



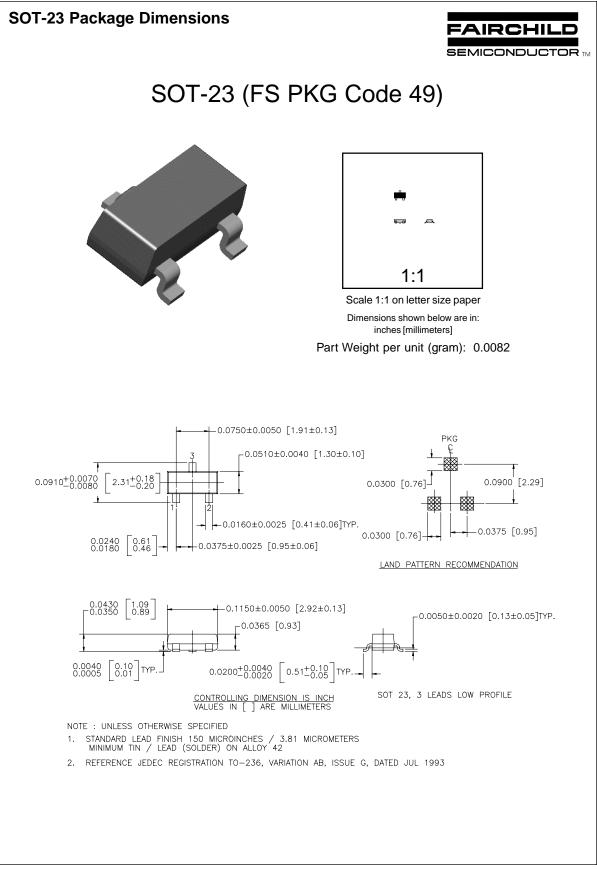


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